

Vishay Siliconix

## 16 $\Omega$ , Low Parasitic Capacitance and Leakage, +12 V / +5 V / +3 V / ± 5 V Quad SPST Switches

### DESCRIPTION

The DG411LE, DG412LE, and DG413LE are monolithic quad single-pole-single-throw analog switches. The DG411LE and DG412LE differ only in that they respond to opposite logic levels. The DG413LE has two normally open and two normally closed switches. It can be given various configurations, including four SPST, two SPDT, and one DPDT.

The DG411LE, DG412LE, and DG413LE offer low on resistance of 16  $\Omega$ , low parasitic capacitance of 15 pF switch on capacitance, and low charge injection over the signal swing range.

The DG411LE, DG412LE, and DG413LE operate on single and dual supplies. Single supply voltage ranges from 3 V to 16 V while dual supply operation is recommended with  $\pm$  3 V to  $\pm$  8 V. Each switch conducts equally well in both direction when on, and blocks input voltages up to the supply levels when off.

The DG411LE, DG412LE, and DG413LE are available in 16 lead TSSOP, SOIC, and PDIP packages.

### FEATURES

- 3 V to 16 V single supply or ± 3 V to ± 8 V dual supply
- On-resistance R<sub>DS(on)</sub>: 16 Ω
- Low parasitic capacitance: C<sub>D(on)</sub>: 15 pF, C<sub>S(off)</sub>: 5 pF
- Less than 8 pC charge injection over the full signal swing range
- Fast switching t<sub>ON</sub>: 16 ns, t<sub>OFF</sub>: 9 ns
- TTL, CMOS compatible
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

Note

This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

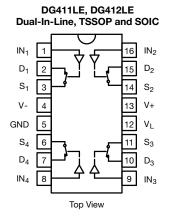
#### BENEFITS

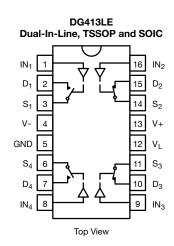
- Wide operation voltage range
- · Low signal errors and distortion
- Fast switching time
- Minimized switching glitch

#### **APPLICATIONS**

- Automatic test equipment
- Data acquisition systems
- Meters and instruments
- Medical and healthcare systems
- Communication systems
- · Audio and video signal routing
- Relay replacement
- · Battery powered systems
- Computer peripherals
- · Audio and video signal routing

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





S23-1120-Rev. C, 11-Dec-2023

ical questions, contact: analogswitchsupport@vish

Document Number: 78091

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LOGIC	DG411LE	DG412LE								
0	On	Off								
1	Off	On								
Logic "0" ≤ 0.8 V										

Logic "1" ≥ 2.4 V

TRUTH TABLE		
LOGIC	SW <sub>1</sub> , SW <sub>4</sub>	SW <sub>2</sub> , SW <sub>3</sub>
0	Off	On
1	On	Off

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

ORDERING INF	ORDERING INFORMATION											
TEMP. RANGE	CONFIGURATION	PACKAGE	PART NUMBER	MIN. ORDER / PACK. QUANTITY								
		16-pin TSSOP	DG411LEDQ-GE3	Tube 360 units								
		10-piil 1330P	DG411LEDQ-T1-GE3	Tape and reel, 3000 units								
	DG411LE	16-pin SOIC	DG411LEDY-GE3	Tube 500 units								
		10-pin 3010	DG411LEDY-T1-GE3	Tape and reel, 2500 units								
		16-pin PDIP	DG411LEDJ-GE3	Tube 500 units								
	DG412LE	16-pin TSSOP	DG412LEDQ-GE3	Tube 360 units								
40.00 1.05.00			DG412LEDQ-T1-GE3	Tape and reel, 3000 units								
-40 °C to +85 °C lead (Pb)-free		16-pin SOIC	DG412LEDY-GE3	Tube 500 units								
		10-pin 3010	DG412LEDY-T1-GE3	Tape and reel, 2500 units								
		16-pin PDIP	DG412LEDJ-GE3	Tube 500 units								
		16-pin TSSOP	DG413LEDQ-GE3	Tube 360 units								
		10-piil 1330P	DG413LEDQ-T1-GE3	Tape and reel, 3000 units								
	DG413LE	16-pin SOIC	DG413LEDY-GE3	Tube 500 units								
		10-pin 3010	DG413LEDY-T1-GE3	Tape and reel, 2500 units								
		16-pin PDIP	DG413LEDJ-GE3	Tube 500 units								

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	LIMIT	UNIT							
V+ to V-		-0.3 to +18							
GND to V-		18							
VL		(GND -0.3) to (V+) +0.3	V						
I <sub>N</sub> <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>	-0.3 to (V+) +0.3 or 30 mA, whichever occurs first	]							
Continuous current (any terminal)		30							
Peak current, S or D (pulsed 1 ms, 10 % du	ty cycle)	100	– mA						
Storago tomporaturo	(DQ, DY suffix)	-65 to +125	°C						
Storage temperature	(AK suffix)	-65 to +150							
	16-pin TSSOP °	450							
Power dissipation (packages) <sup>b</sup>	16-pin SOIC <sup>d</sup>	650	mW						
	16-pin CerDIP <sup>e</sup>	900							
ESD human body model (HBM); per ANSI /	ESDA / JEDEC <sup>®</sup> JS-001	2500	V						
Latch up current, per JESD78D		400	mA						

Notes

- a. Signals on S<sub>X</sub>, D<sub>X</sub>, or IN<sub>X</sub> exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings b. All leads welded or soldered to PC board
- c. Derate 7 mW/°C above 75 °C

d. Derate 7.6 mW/°C above 75 °C

e. Derate 12 mW/°C above 75 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

S23-1120-Rev. C, 11-Dec-2023



## DG411LE, DG412LE, DG413LE

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		TEST CONDITIONS			ΔSI	IFFIX	D SI	IFFIX	
		UNLESS OTHERWISE			LIN	IITS	LIN		
PARAMETER	SYMBOL	SPECIFIED	TEMP. <sup>b</sup>	TYP. °	-55 °C to +125 °C		-40 °C to +85 °C		UNIT
					MIN. d	MAX. d	MIN. <sup>d</sup>	MAX. d	
Analog Switch									-
Analog signal range <sup>e</sup>	VANALOG		Full	-	0	12	0	12	V
Drain-source on-resistance	Base	V+ = 10.8 V, V- = 0 V	Room	16	-	26	-	26	Ω
	R <sub>DS(on)</sub>	$I_{\rm S}$ = 10 mA, $V_{\rm D}$ = 2/9 V	Full	-	-	40	-	35	52
			Room	-	-1	1	-1	1	
Quitch off lookage ourrent	I <sub>S(off)</sub>		Full	-	-15	15	-10	10	
Switch off leakage current		V <sub>D</sub> = 1/11 V, V <sub>S</sub> = 11/1 V	Room	-	-1	1	-1	1	
	I <sub>D(off)</sub>		Full	-	-15	15	-10	10	nA
		V <sub>S</sub> = V <sub>D</sub> = 11/1 V	Room	-	-1	1	-1	1	
Channel on leakage current	I <sub>D(on)</sub>		Full	-	-15	15	-10	10	
Digital Control									
Input current, VIN Low	IIL	V <sub>IN</sub> under test = 0.8 V	Full	0.01	-1.5	1.5	-1	1	
Input current, VIN High	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full		-1.5	1.5	-1	1	μA
Dynamic Characteristics				1		1	L		
Turn-on time	t <sub>ON</sub>	$R_{\rm L} = 300 \ \Omega, \ C_{\rm L} = 35 \ \rm pF,$	Room	16	-	50	-	50	
			Full	-	-	70	-	60	
		$V_{\rm S} = 5 \text{ V}$ , see figure 2	Room	9	-	30	_	30	
Turn-off time	t <sub>OFF</sub>		Full	-	_	48	_	40	ns
Break-before-make time		DG413L only, V <sub>S</sub> = 5 V,	-	_		_		-	
delay	t <sub>D</sub>	$R_L = 300 \Omega$ , $CL = 35 pF$	Room	5	-	-	-	-	
Charge injection <sup>e</sup>	Q	$V_g = 0 V, R_g = 0 \Omega, C_L = 10 nF$	Room	6.6	-	-	-	-	рC
Off-isolation <sup>e</sup>	OIRR		Room	68.4	-	-	-	-	
Channel-to-channel crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ , f = 1 MHz	Room	114	-	-	-	-	dE
Source off capacitance e	C <sub>S(off)</sub>		Room	5	-	-	-	-	
Drain off capacitance e	C <sub>D(off)</sub>	f = 1 MHz	Room	6	-	-	-	-	pF
Channel-on capacitance e	C <sub>D(on)</sub>		Room	15	-	-	-	-	
Power Supplies	2(01)					1			
Deall' second			Room	0.02	-	1	-	1	
Positive supply current	I+		Full	-	-	7.5	-	5	1
N 0 1 1			Room	-0.002	-1	-	-1	-	1
Negative supply current	I-		Full	-	-7.5	-	-5	-	1
		$V_{IN} = 0 V \text{ or } 5 V$	Room	0.002	-	1	-	1	μA
Logic supply current	١L		Full	-	-	7.5	-	5	1
	I <sub>GND</sub>		Room	-0.002	-1	-	-1	-	
Ground current			Full	-	-7.5	_	-5		1

Notes

a. Refer to PROCESS OPTION FLOWCHART

b. Room = 25 °C, full = as determined by the operating temperature suffix

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

e. Guaranteed by design, not subject to production test

f.  $V_{IN}$  = input voltage to perform proper function

g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



# DG411LE, DG412LE, DG413LE

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SPECIFICATIONS a (	Dual Supp	ly ± 5 V)							
PARAMETER	SYMBOL			TYP. °	LIN	<b>IFFIX</b> <b>IITS</b> 0 +125 °C	LIN	<b>IFFIX</b> IITS 0 +85 °C	UNIT
		V+ = 5 V, V- = -5 V V <sub>L</sub> = 5 V, V <sub>IN</sub> = 2.4 V, 0.8 V <sup>f</sup>			MIN. d	MAX. d	MIN. <sup>d</sup>	MAX. d	
Analog Switch				•					
Analog signal range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	-5	5	-5	5	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V+ = 5 V, V- = -5 V, I <sub>S</sub> = 10 mA, V <sub>D</sub> = ± 3.5 V	Room Full	18	-	30 42	-	30 37	Ω
			Room	-	-1	1	-1	1	
	I <sub>S(off)</sub>	V+ = 5.5, V- = -5.5 V,	Full	-	-15	15	-10	10	
Switch off leakage current <sup>g</sup>		$V_{\rm D} = \pm 4.5 \text{ V}, V_{\rm S} = \pm 4.5 \text{ V}$	Room	-	-1	1	-1	1	
	I <sub>D(off)</sub>		Full	-	-15	15	-10	10	nA
		V+ = 5.5 V, V- = -5.5 V,	Room	-	-1	1	-1	1	
Channel on leakage current <sup>g</sup>	I <sub>D(on)</sub>	$V_{\rm S} = V_{\rm D} = \pm 4.5 \text{ V}$	Full	-	-15	15	-10	10	
Digital Control									
Input current, V <sub>IN</sub> low <sup>e</sup>	١ <sub>١L</sub>	V <sub>IN</sub> under test = 0.8 V	Full	0.05	-1.5	1.5	-1	1	
Input current, V <sub>IN</sub> high <sup>e</sup>	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.05	-1.5	1.5	-1	1	μA
Dynamic Characteristics					1		1	I.	
			Room	17	-	50	-	50	
Turn-on time <sup>e</sup>	t <sub>ON</sub>	$R_L = 300 \Omega$ , $C_L = 35 pF$ ,	Full	-	-	70	-	60	
		$V_{\rm S} = \pm 3.5$ V, see figure 2		12	-	35	-	35	- 
Turn-off time <sup>e</sup>	t <sub>OFF</sub>		Full	-	-	50	-	40	ns
Break-before-make time delay <sup>e</sup>	t <sub>D</sub>	DG413L only, V <sub>S</sub> = 3.5 V, $R_L$ = 300 $\Omega$ , C <sub>L</sub> = 35 pF	Room	5	-	-	-	-	
Charge injection <sup>e</sup>	Q	$V_{g} = 0 V, R_{g} = 0 \Omega, C_{L} = 10 nF$	Room	5.8	-	-	-	-	рС
Off isolation <sup>e</sup>	OIRR		Room	68	-	-	-	-	
Channel-to-channel crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 $ Ω, $C_L = 5 $ pF, f = 1 MHz	Room	113	-	-	-	-	dB
Source off capacitance e	C <sub>S(off)</sub>		Room	5	-	-	-	-	
Drain off capacitance e	C <sub>D(off)</sub>	f = 1 MHz	Room	6	-	-	-	-	pF
Channel on capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	14	-	-	-	-	
Power Supplies									
Positive supply current <sup>e</sup>	l+		Room	0.03	-	1	-	1	
	1+		Full	-	-	7.5	-	5	1
Negative supply current <sup>e</sup>	I-		Room	-0.002	-1	-	-1	-	
negative supply current °	1-	V <sub>IN</sub> = 0 V or 5 V	Full	-	-7.5	-	-5	-	μA
Logic supply current <sup>e</sup>	I.		Room	0.002	-	1	-	1	μΑ
	ΙL		Full	-	-	7.5	-	5	
Ground current <sup>e</sup>			Room	-0.002	-1	-	-1	-	
	I <sub>GND</sub>		Full	-	-7.5	-	-5	-	

Notes

a. Refer to PROCESS OPTION FLOWCHART

b. Room = 25 °C, full = as determined by the operating temperature suffix

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

e. Guaranteed by design, not subject to production test

f. V<sub>IN</sub> = input voltage to perform proper function

g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



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SPECIFICATIONS <sup>a</sup> (Single Supply 5 V)										
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 5 V, V- = 0 V		TYP. ℃	LIN -55 °C	<b>IFFIX</b> II <b>TS</b> to +125 C	LIN	IFFIX IITS o +85 °C	UNIT	
		$V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^{f}$			MIN. <sup>d</sup>	MAX. d	MIN. d	MAX. <sup>d</sup>		
Analog Switch										
Analog signal range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	-	5	-	5	V	
Drain-source on-resistance <sup>e</sup>	P	V+ = 4.5 V,	Room	36	-	50	-	50	Ω	
Drain-source on-resistance -	R <sub>DS(on)</sub>	I <sub>S</sub> = 5 mA, V <sub>D</sub> = 1 V, 3.5 V	Full	-	-	88	-	75	52	
Dynamic Characteristics										
Turn-on time <sup>e</sup>	+		Room	27	-	50	-	50		
	t <sub>ON</sub>	$R_L = 300 \Omega$ , $C_L = 35 pF$ ,	Hot	-	-	90	-	60	ns	
Turn-off time <sup>e</sup>	t <sub>OFF</sub>	$V_{S} = 3.5 V$ , see figure 2	Room	15	-	30	-	30		
			Hot	-	-	55	-	40		
Break-before-make time delay <sup>e</sup>	t <sub>D</sub>	DG413L only, $V_S = 3.5 V$ , R <sub>L</sub> = 300 $\Omega$ , C <sub>L</sub> = 35 pF	Room	11	-	-	-	-		
Charge injection <sup>e</sup>	Q	$V_{g} = 0 V, R_{g} = 0 \Omega, C_{L} = 10 nF$	Room	3.3	-	-	-	-	рС	
Power Supplies										
Positive supply current <sup>e</sup>	l+		Room	0.02	-	1	-	1		
Positive supply current -	1+		Hot	-	-	7.5	-	5		
Negative supply current <sup>e</sup>	-		Room	-0.002	-1	-	-1	-		
Negative supply current -	1-	V <sub>IN</sub> = 0 V or 5 V	Hot	-	-7.5	-	-5	-		
Logic supply current e	I.	$v_{\rm IN} = 0$ V or 5 V	Room	0.002	-	1	-	1	μA	
Logic supply current *	١L		Hot	-	-	7.5	-	5		
Ground current <sup>e</sup>	laura.		Room	-0.002	-1	-	-1	-		
	'GND	IGND		-	-7.5	-	-5	-		

#### Notes

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e. Guaranteed by design, not subject to production test

f.  $V_{IN}$  = input voltage to perform proper function

g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



## DG411LE, DG412LE, DG413LE

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SPECIFICATIONS a (Single Supply 3 V)										
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. <sup>b</sup>	TYP. °	-55 °C	<b>to</b> +125 C	LIM	IFFIX IITS o +85 °C	UNIT	
		V+ = 3 V, V- = 0 V $V_L = 3 V, V_{IN} = 0.4 V, 2.0 V^{f}$			MIN. d	MAX. d	MIN. d	MAX. d		
Analog Switch										
Analog signal range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	0	3	0	3	V	
Drain-source on-resistance	<b>D</b>	V+ = 3.0 V, V- = 0 V,	Room	71	52	90	52	90	Ω	
Dialit-Source off-resistance	R <sub>DS(on)</sub>	$I_{S} = 5 \text{ mA}, V_{D} = 0.5, 2.2 \text{ V}$	Full	-	-	110	-	102	52	
			Room	-	-1	1	-1	1		
Switch off leakage current <sup>g</sup>	I <sub>S(off)</sub>	V+ = 3.3, V- = 0 V,	Full	-	-15	15	-10	10		
Switch on leakage current s	I	$V_D = 1, 2 V, V_S = 2, 1 V$	Room	-	-1	1	-1	1	nA	
	I <sub>D(off)</sub>		Full	-	-15	15	-10	10		
Channel on leakage current <sup>g</sup>	I <sub>D(on)</sub>	V+ = 3.3 V, V- = 0 V,	Room	-	-1	1	-1	1	-	
Channel on leakage current 9		$V_{\rm S} = V_{\rm D} = 1, 2  {\rm V}$	Full	-	-15	15	-10	10		
Digital Control										
Input current, V <sub>IN</sub> low	١ <sub>١</sub> ٢	V <sub>IN</sub> under test = 0.4 V	Full	0.005	-1.5	1.5	-1	1	μA	
Input current, V <sub>IN</sub> high	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.005	-1.5	1.5	-1	1	μΑ	
Dynamic Characteristics										
Turn-on time	t <sub>ON</sub>		Room	57	-	85	-	85		
rum-on time	LON	$R_L = 300 \Omega$ , $C_L = 35 pF$ ,	Full	-	-	150	-	110		
Turn-off time	+	$V_{S} = 1.5 V$ , see figure 2	Room	25	-	60	-	60	ns	
rum-on time	t <sub>OFF</sub>		Full	-	-	100	-	85	110	
Break-before-make time delay	t <sub>D</sub>	DG413L only, $V_S = 1.5 V$ , R <sub>L</sub> = 300 $\Omega$ , C <sub>L</sub> = 35 pF	Room	24	-	-	-	-		
Charge injection <sup>e</sup>	Q	$V_g = 0 V, R_g = 0 \Omega, C_L = 10 nF$	Room	2	-	-	-	-	рС	
Off isolation <sup>e</sup>	OIRR		Room	68	-	-	-	-		
Channel-to-channel crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ , f = 1 MHz	Room	107	-	-	-	-	dB	
Source off capacitance e	C <sub>S(off)</sub>		Room	6	-	-	-	-		
Drain off capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	7	-	-	-	-	pF	
Channel on capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	15	-	-	-	-		

Notes

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d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

e. Guaranteed by design, not subject to production test

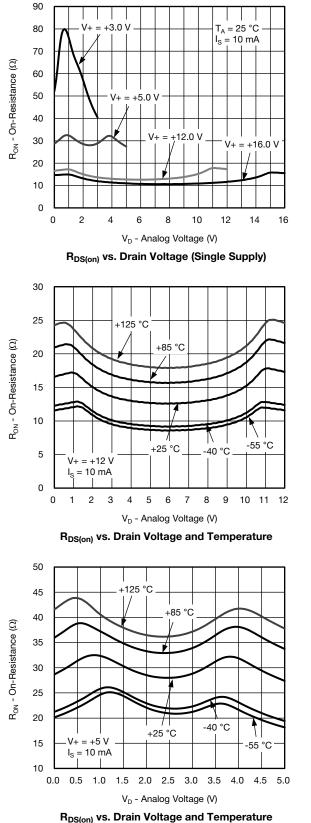
f.  $V_{IN}$  = input voltage to perform proper function

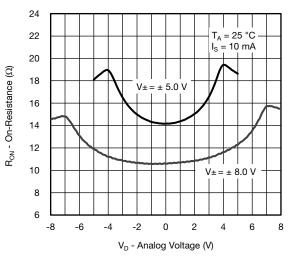
g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



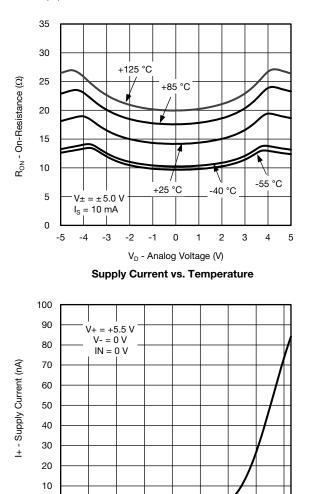
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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





R<sub>DS(on)</sub> vs. Drain Voltage and Temperature (Single Supply)



 R<sub>DS(on)</sub> vs. Drain Voltage and Temperature
 Switching Time vs. Single Supply

 S23-1120-Rev. C, 11-Dec-2023
 7

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0

-40

-20

0

20

40

Temperature (°C)

60

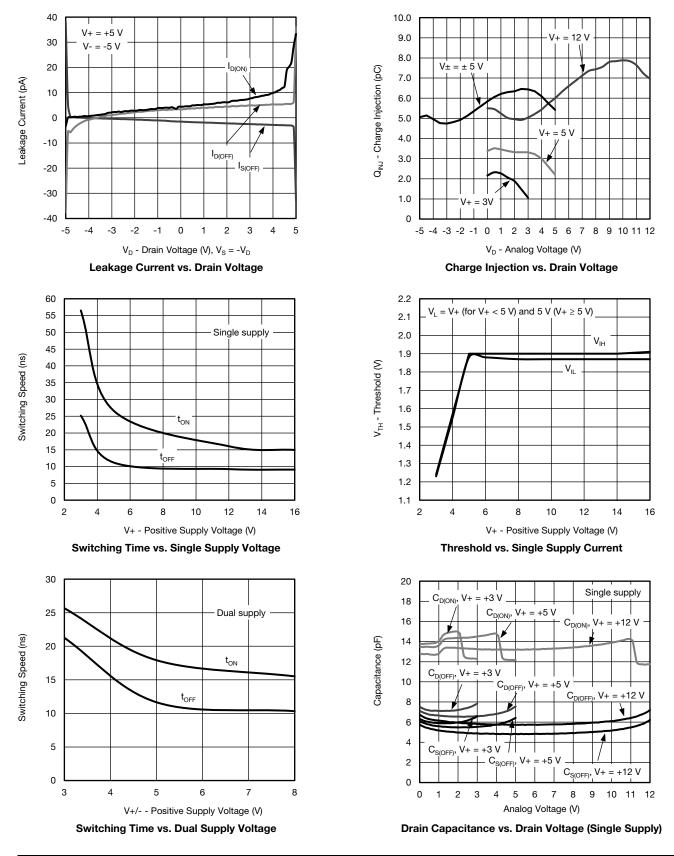
80

100



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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



S23-1120-Rev. C, 11-Dec-2023

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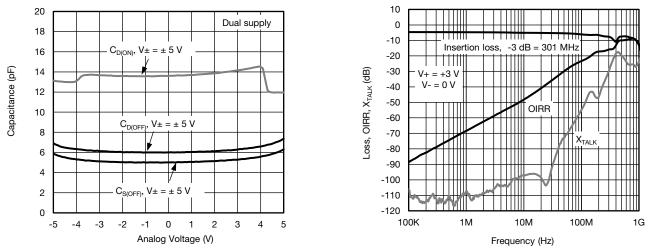
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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Drain Capacitance vs. Drain Voltage (Dual Supply)

Insertion Loss, Off Isolation and Crosstalk vs. Frequency

### SCHEMATIC DIAGRAM (Typical Channel)

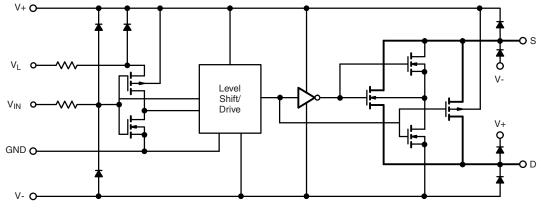


Fig. 1

S23-1120-Rev. C, 11-Dec-2023

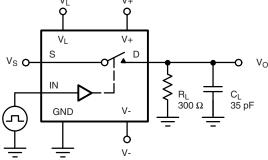
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## DG411LE, DG412LE, DG413LE

Vishay Siliconix

### **TEST CIRCUITS**

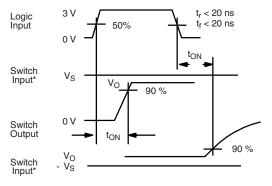
**VISHAY** 



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CL (includes fixture and stray capacitance)

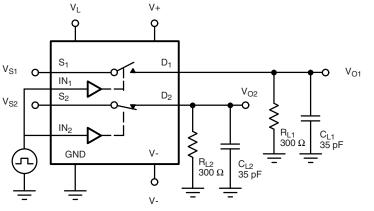


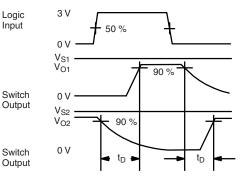


Note: Logic input waveform is inverted for switches that have the opposite logic sense control

Logic Input

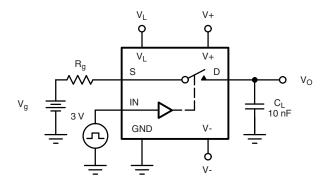


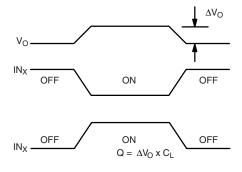




C<sub>L</sub> (includes fixture and stray capacitance)

#### Fig. 3 - Break-Before-Make (DG413LE)

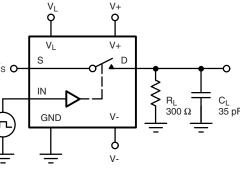




Document Number: 78091

 $\ensuremath{\mathsf{IN}_X}$  dependent on switch configuration Input polarity determined by sense of switch.

Fig. 4 - Charge Injection









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### **TEST CIRCUITS**

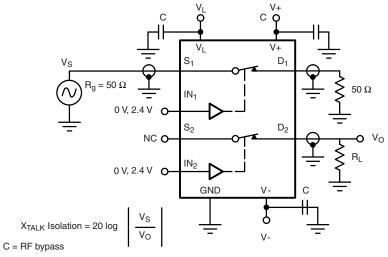
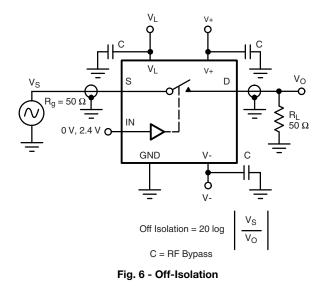


Fig. 5 - Crosstalk



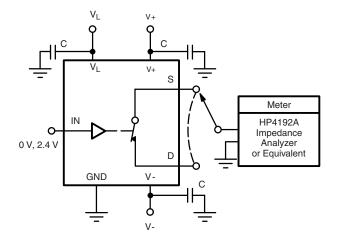


Fig. 7 - Source / Drain Capacitances



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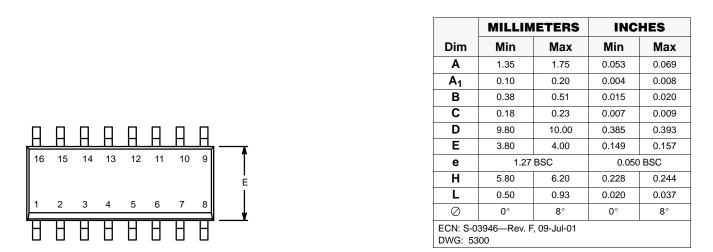
PRODUC	T SUMMA	RY							
Part number	DG411LE	DG411LE	DG411LE	DG412LE	DG412LE	DG412LE	DG413LE	DG413LE	DG413LE
Status code	2	2	2	2	2	2	2	2	2
Configuration	SPST x 4, NC	SPST x 4, NC	SPST x 4, NC	SPST x 4, NO	SPST x 4, NO	SPST x 4, NO	SPST x 4, comp	SPST x 4, comp	SPST x 4, comp
Single supply min. (V)	3	3	3	3	3	3	3	3	3
Single supply max. (V)	16	16	16	16	16	16	16	16	16
Dual supply min. (V)	3	3	3	3	3	3	3	3	3
Dual supply max. (V)	8	8	8	8	8	8	8	8	8
On-resistan ce (Ω)	16	16	16	16	16	16	16	16	16
Charge injection (pC)	6.6	6.6	6.6	6.6	6.6	6.6	6.6	6.6	6.6
Source on capacitance (pF)	15	15	15	15	15	15	15	15	15
Source off capacitance (pF)	5	5	5	5	5	5	5	5	5
Leakage switch on typ. (nA)	-	-	-	-	-	-	-	-	-
Leakage switch off max. (nA)	1	1	1	1	1	1	1	1	1
-3 dB bandwidth (MHz)	-	-	-	-	-	-	-	-	-
Package	Plastic DIP-16	SO-16 (narrow) AS	TSSOP-16	TSSOP-16	SO-16 (narrow) AS	Plastic DIP-16	TSSOP-16	Plastic DIP-16	SO-16 (narrow) AS
Functional circuit / applications	Multi purpose, instrumentation, medical and healthcare, portable								
Interface	Parallel								
Single supply operation	Yes								
Dual supply operation	Yes								
Turn on time max. (ns)	50	50	50	50	50	50	50	50	50
Crosstalk and off isolation	-114	-114	-114	-114	-114	-114	-114	-114	-114

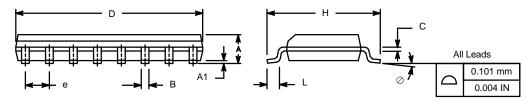
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SOIC (NARROW): 16-LEAD

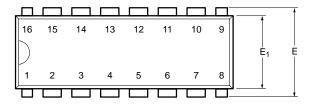
JEDEC Part Number: MS-012

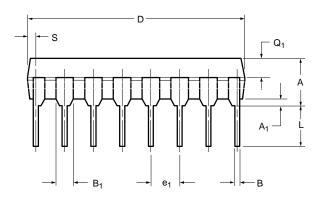


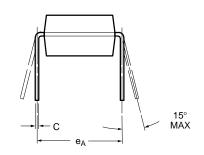




### PDIP: 16-LEAD







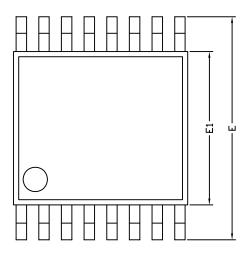
	MILLIN	IETERS	INC	HES					
Dim	Min	Max	Min	Max					
Α	3.81	5.08	0.150	0.200					
A <sub>1</sub>	0.38	1.27	0.015	0.050					
В	0.38	0.51	0.015	0.020					
B <sub>1</sub>	0.89	1.65	0.035	0.065					
С	0.20	0.30	0.008	0.012					
D	18.93	21.33	0.745	0.840					
E	7.62	8.26	0.300	0.325					
E <sub>1</sub>	5.59	7.11	0.220	0.280					
<b>e</b> <sub>1</sub>	2.29	2.79	0.090	0.110					
e <sub>A</sub>	7.37	7.87	0.290	0.310					
L	2.79	3.81	0.110	0.150					
Q <sub>1</sub>	1.27	2.03	0.050	0.080					
S	0.38	1.52	.015	0.060					
	ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482								

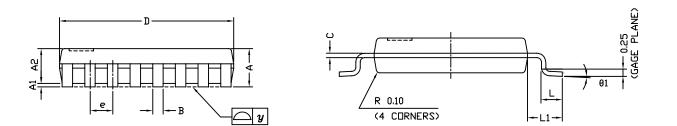


# Package Information

Vishay Siliconix

### TSSOP: 16-LEAD





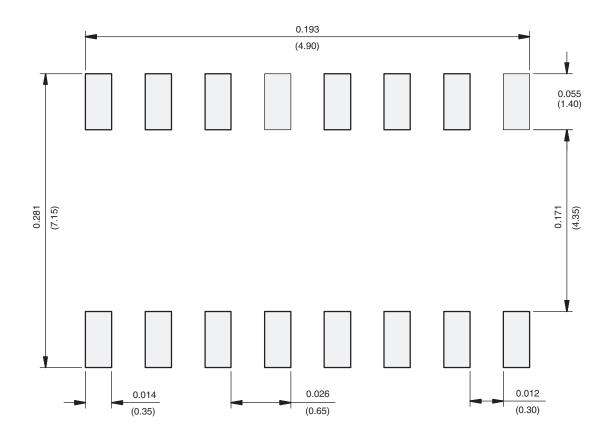
	C	IMENSIONS IN MILLIMETE	RS
Symbols	Min	Nom	Max
A	-	1.10	1.20
A1	0.05	0.10	0.15
A2	-	1.00	1.05
В	0.22	0.28	0.38
С	-	0.127	-
D	4.90	5.00	5.10
E	6.10	6.40	6.70
E1	4.30	4.40	4.50
е	-	0.65	-
L	0.50	0.60	0.70
L1	0.90	1.00	1.10
у	-	-	0.10
θ1	0°	3°	6°
ECN: S-61920-Rev. D, 23 DWG: 5624	-Oct-06		



**PAD** Pattern

Vishay Siliconix

### **RECOMMENDED MINIMUM PAD FOR TSSOP-16**



Recommended Minimum Pads Dimensions in inches (mm)

# **Application Note 826**

Vishay Siliconix



### **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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Revision: 01-Jul-2024